



BrightLase® Fiber Coupled Single Mode Laser

Features

- High power single mode
- TEC, Photodiode and Thermistor options
- 1550 nm
- PM fiber delivery optional

Benefits

- Reduces number of system components and amplifying stages
- Enables low cost direct diode replacement of CW solid state lasers
- Excellent frequency doubling efficiency possible
- Longer working distance, simpler optical design

Applications

- Fiber laser seeding
- Direct materials processing
- Laser communications and rangefinding



PARAMETER	7115-0000	7115-0001
Center Wavelength	1550 nm	1550 nm
Center Wavelength Tolerance	±5 nm	±5 nm
Output Power from fiber	400 mW CW	5W peak Pulsed
Spectral width (FWHM)	< 0.1nm FWHM	< 0.1nm FWHM
Temperature tuning coefficient	0.08 nm/°C	0.08 nm/°C
Pulse length	CW	20 nsec
Rep rate	CW	1MHz
Operating Current Amp section	< 4.0 A	< 27 A
Operating Current Osc section	< 0.7 A	< 0.7 A
Operating Voltage Amp Section	< 1.9 V	TBD
Operating Voltage Osc. Section	< 3.9 V	TBD
Photodiode responsivity	>2uA/mW	TBD
Photodiode dark current	>800uA	TBD
Thermistor	10kOhm	10kOhm
TEC current	TBD	TBD
TEC voltage	TBD	TBD
ESD protection (HBM)	400V	400V
Case	Floating	Floating
Operating Temperature	20 °C	20 °C
Fiber	SMF	SMF
Fiber length	1 meter	1 meter
Fiber jacketing	900µm jacket	900µm jacket
Fiber connector	SC	SC
Fiber bend radius	25mm	25mm
Storage temperature	-40 to +85 degC	-40 to +85 degC
Relative humidity, non-condensing	5% to 90%	5% to 90%

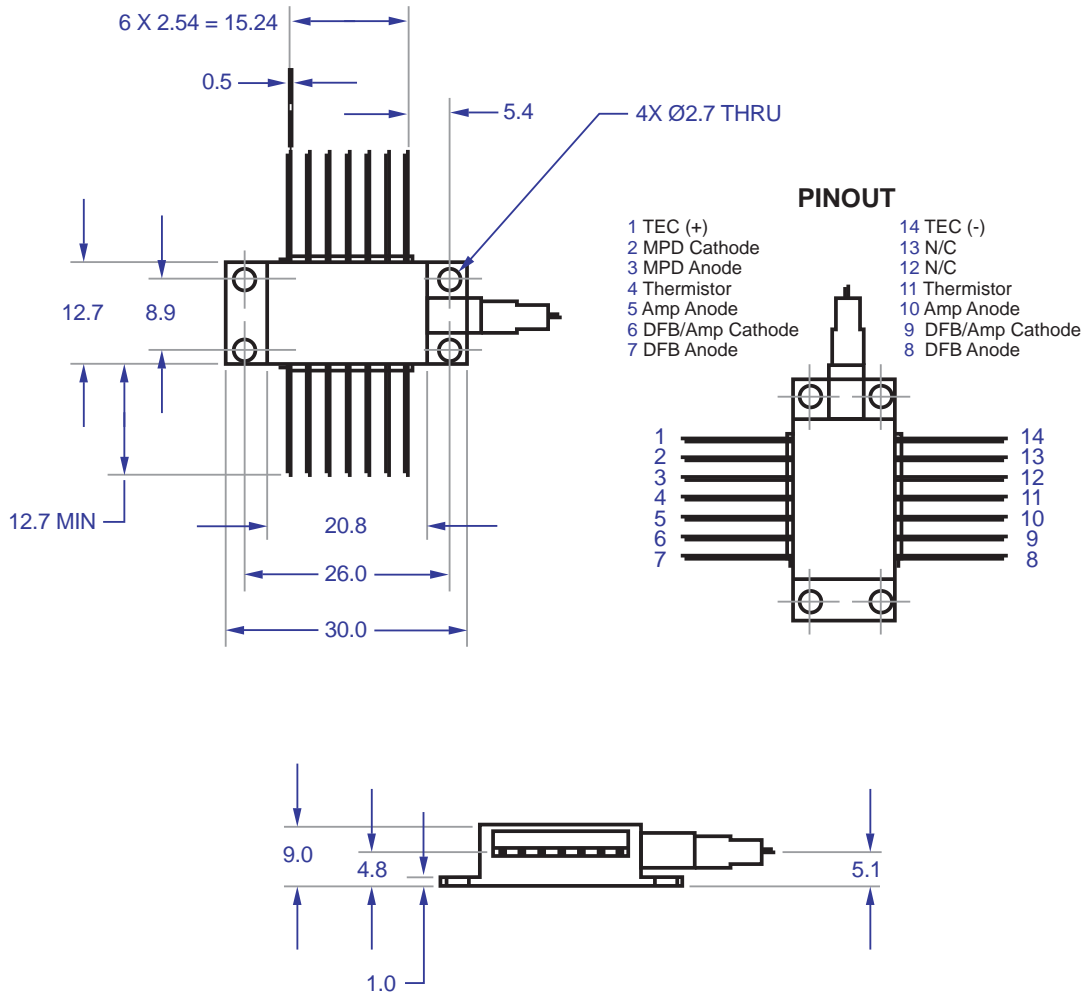
BRIGHTNESS and POWER
Breaking Performance Barriers through Semiconductor Laser Innovation

QPC Lasers, Inc.





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光技術をサポートする

株式会社オプトサイエンス

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